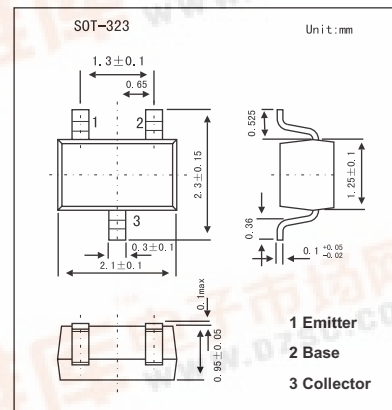


SMD Type Transistors

High-Voltage Amplifier Transistor
2SA1579

■ Features

- High breakdown voltage.



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector-base voltage	V _{CB0}	-120	V
Collector-emitter voltage	V _{CEO}	-120	V
Emitter-base voltage	V _{EBO}	-5	V
Collector current	I _c	-50	mA
Collector power dissipation	P _c	0.2	W
Junction temperature	T _j	150	°C
Storage temperature	T _{stg}	-55 to +150	°C

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector-base breakdown voltage	BV _{CB0}	I _c =-50μA	-120			V
Collector-emitter breakdown voltage	BV _{CEO}	I _c =-1mA	-120			V
Emitter-base breakdown voltage	BV _{EBO}	I _E =-50μA	-5			V
Collector cutoff current	I _{cBO}	V _{CB} =-100V			-0.5	μA
Emitter cutoff current	I _{EBO}	V _{EB} =-4V			-0.5	μA
Collector-emitter saturation voltage	V _{CE(sat)}	I _c =-10mA, I _b =-1mA			-0.5	V
DC current transfer ratio	h _{FE}	V _{CE} =-6V, I _c =-2mA	180		560	
Output capacitance	f _T	V _{CE} =-12V, I _E = 2mA, f=100MHz		140		MHz
Transition frequency	C _{ob}	V _{CB} =-12V, I _E =0A, f=1MHz		3.2		pF

■ hFE Classification

Marking	RR	RS
Rank	R	S
	180~390	270~560

